



PRODUCT NAME : PH2369 NPN General Purpose Transistor (Pack of 5)

PRICE : Rs 39.00

SKU : RM2158



NOTE: THE PRODUCT MAY BE DIFFERENT FROM IMAGE SHOWN. Copyrights by Robomart.com

DESCRIPTION

Features

- Collector-Emitter Volt (V_{ce0}): 15V
- Collector-Base Volt (V_{cb0}): 40V
- Collector Current (I_c): 0.2A
- h_{fe} : 40-120 @ 10mA
- Power Dissipation (P_{tot}): 500mW
- Current-Gain-Bandwidth (f_{total}): 500MHz
- Type: PNP

NPN switching transistor

PH2369

FEATURES

- Low current (max. 200 mA)
- Low voltage (max. 15 V).

APPLICATIONS

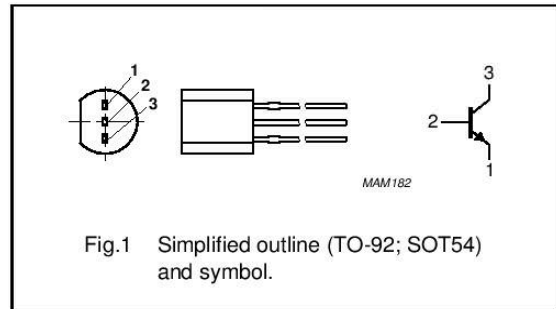
- High-speed switching.

DESCRIPTION

NPN switching transistor in a TO-92; SOT54 plastic package.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	40	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	4.5	V
I_C	collector current (DC)		–	200	mA
I_{CM}	peak collector current		–	300	mA
I_{BM}	peak base current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	500	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

NPN switching transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	250	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 20\text{ V}$	–	400	nA
		$I_E = 0; V_{CB} = 20\text{ V}; T_j = 125\text{ °C}$	–	30	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 4\text{ V}$	–	100	nA
h_{FE}	DC current gain	$I_C = 10\text{ mA}; V_{CE} = 1\text{ V}$	40	120	
		$I_C = 10\text{ mA}; V_{CE} = 1\text{ V}; T_{amb} = -55\text{ °C}$	20	–	
		$I_C = 100\text{ mA}; V_{CE} = 2\text{ V}$	20	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	–	250	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	700	850	mV
C_c	collector capacitance	$I_E = I_C = 0; V_{CB} = 5\text{ V}; f = 1\text{ MHz}$	–	4	pF
C_e	emitter capacitance	$I_C = I_E = 0; V_{EB} = 1\text{ V}; f = 1\text{ MHz}$	–	4.5	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	500	–	MHz

Switching times (between 10% and 90% levels)

t_{on}	turn-on time	$I_{Con} = 10\text{ mA}; I_{Bon} = 3\text{ mA}; I_{Boff} = -1.5\text{ mA};$ see Fig.2 test conditions A	–	10	ns
t_d	delay time		–	4	ns
t_r	rise time		–	6	ns
t_{off}	turn-off time		–	20	ns
t_s	storage time		–	10	ns
t_f	fall time		–	10	ns
t_{on}	turn-on time	$I_{Con} = 100\text{ mA}; I_{Bon} = 40\text{ mA}; I_{Boff} = -20\text{ mA};$ see Fig.2 test conditions B	–	13	ns
t_{off}	turn-off time		–	35	ns

